SOT-23 Current Sensing IC

Features

- VDS(on) or VCE(on) sensing
- Eliminates external current sensing resistors
- Enables inductance-less current sensing
- 600V blocking capability
- Programmability and temperature compensation possible
- No VCC required
- Gate drive on/off sync input
- Filter delay at GATE turn-on (200nsec typ.)
- 20.8V zener clamps on GATE and CS pins
- Integrated ESD protection and latch immunity on all pins
- Tiny 5-pin SOT-23 package

Applications

- MOSFET, DirectFET, or IGBT current sensing
- Over-current protection
- Industrial applications
- Motor control
- Power tools
- Brick converters
- Forklifts
- Induction heating

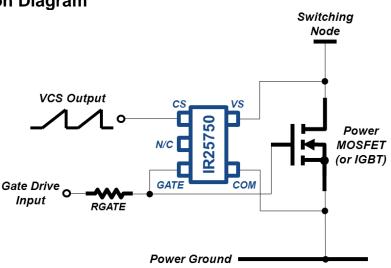
Typical Connection Diagram

Description

The IR25750L is a novel current sensing IC that extracts the VDS(on) of a power MOSFET, or the VCE(on) of an IGBT, during the switch on-time. IR's proprietary 600V HVIC technology then blocks the high drain voltage to during the MOSFET or IGBT off-time. This IC allows for external current sensing resistors to be eliminated for reducing power losses and increasing overall system efficiency. The IC includes a gate drive input that provides VCC supply voltage to the IC and synchronizes the internal sensing circuit to and off times of the the on switch. Programmability and temperature compensation are also possible.

Package Options





Ordering Information

Daga Dart Number	Deckers True	Standard Pack		Ondenskie Deut Neuerken	
Base Part Number	Package Type	Form	Quantity	Orderable Part Number	
IR25750LPBF	SOT23-5L	Tape and Reel	3000	IR25750LTRPBF	

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Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any pin. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition		Min	Max	Units
Vs	VS pin voltage		-20 [†]	625	
V _{GATE}	GATE pin voltage		-0.3	V _{CLAMP} ^{††}	V
V _{CS}	CS pin voltage		-0.5	VCLAMP	
PD	Package power dissipation @ Ta \leq +25 ^{o}C	5L SOT-23	—	250	mW
RΘ _{JA}	Thermal resistance, junction to ambient	5L SOT-23	—	191	°C/W
TJ	Junction temperature		-55	150	
Ts	Storage temperature		-00	130	٥C
TL	IC pin temperature (soldering, 10 seconds)			300	

† The test condition for the minimum –VS rating is for a pulse width of 1usec. Larger pulse widths will result in a lower –VS voltage rating.

†† This IC contains a 20.8V voltage clamp structure between the GATE and COM pins, and, between the CS and COM pins. Please note that this pin should not be driven by a DC, low impedance power source greater than the VCLAMP specified in the Electrical Characteristics section.

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions.

Symbol	Definition	Min	Max	Units
Vs	VS pin voltage	-5.0	600	
V _{GATE}	GATE pin voltage	COM	M	V
V _{CS}	CS pin voltage	СОМ	V _{CLAMP}	
TJ	Junction temperature	-40	125	٥C



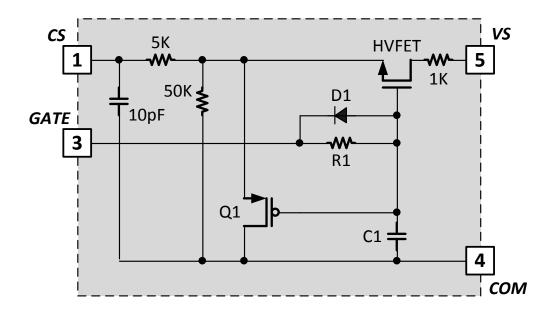
Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified. All parameters are referenced to COM.

Symbol	Definition	Min	Тур	Max	Units	Test Conditions	
GATE Pin C	GATE Pin Characteristics						
t _{DLY}	GATE-to-CS rising-edge blank delay time	_	200	_	nsec	V _{GATE} = rising edge	
V _{CLAMP1}	GATE pin internal Zener clamp voltage	21.1	22.5	24.0	V	$I_{GATE} = 1mA$	
High-Voltag	High-Voltage Switching Node Input (VS Pin) Characteristics						
I _{LK}	Offset supply leakage current	_	_	50	μA	$V_{GATE} = COM,$ $V_{S} = 600V$	
R _{VS_CS}	VS-to-CS 'ON' resistance	_	6.2	_	kΩ	$V_{GATE} = 15V$	
CS Pin Characteristics							
V _{CS_LOW}	CS pin voltage during GATE pin 'low' state	_	СОМ	_	V	$V_{GATE} = COM$	
V _{CLAMP2}	CS pin internal Zener clamp voltage	_	20.8	_		I _{CS} = 1mA	

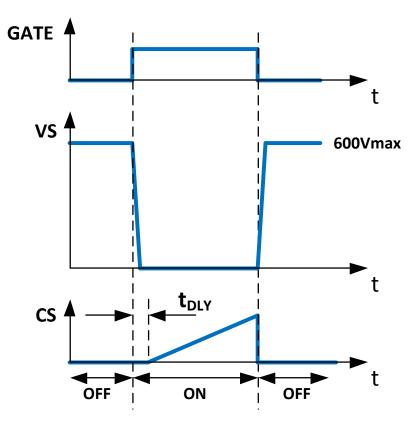


Functional Block Diagram





Timing Diagram

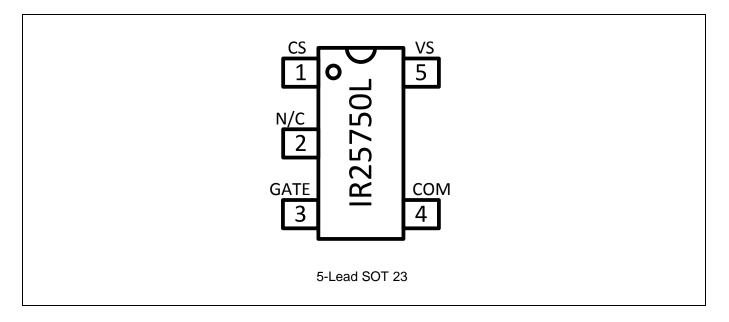




Pin Definitions

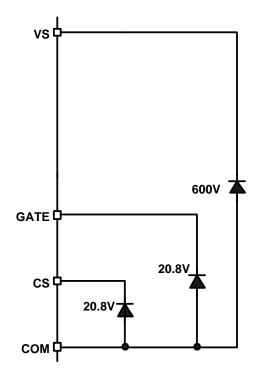
Pin	Symbol	Description	
1	CS	Current sense output	
2	N/C	No connect	
3	GATE	/CC supply and on/off sync input	
4	СОМ	IC ground	
5	VS	Switch drain or collector input sensing node	

Pin Assignments





Input / Output Pin Equivalent Circuit Diagrams



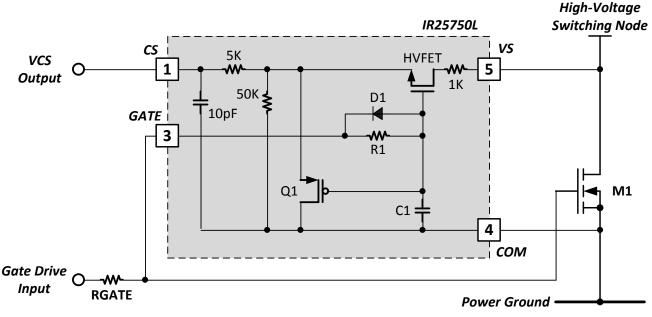


Functional Description

I. General Description

The IR25750L current sensing circuit eliminates the traditional series-connected sensing resistor and is connected instead in parallel to the power switch. The circuit measures the VDS(on) of the switching power MOSFET or VCE(on) of an IGBT. The IC has four external connection nodes (VS, GATE, CS, COM) and includes (Figure 1): a 600V MOSFET (HVFET); an RC-delay circuit (R1, C1, D1); and a PMOS hold-down transistor (Q1). The circuit does not require a VCC supply node and instead utilizes the existing gate drive signal for powering and turning the circuit on and off. During the off-time of the external power switch (M1), the gate drive signal is at COM, the HVFET is off, Q1 is on, and the CS node is held at COM. Since the internal HVFET is off, any high voltage occurring at the drain of the power MOSFET (600Vmax) will be safely blocked by the HVFET from the rest of the low-voltage circuitry. When M1 is turned on by the gate drive signal, the drain voltage of M1 will decrease to a level given by the VDS(on) of M1. After a short delay time (200nsec, typical) set by the internal R-C delay block (R1, C1), the gate voltage of the HVFET rises up and turns the HVFET on. Q1 turns off, therefore releasing the CS output pin. The VDS(on) of M1 is then transmitted from the VS pin, through the HVFET, to the CS output pin. There is an internal voltage divider formed by a 1Kohm resistor at the VS pin, the RDS(on) of the HVFET (0.2Kohm), and a 50Kohm resistor from the source of HVFET to COM. The ratio of this resistor divider is approximately unity (50/51.2), resulting an excellent matching from the VS pin to the CS pin. A small series R-C filter (5K and 10pF) also exists at the CS pin to help suppress high-frequency noise. Also, important to note, to avoid internal high-voltage damage to the IC, the IR25750L must always turn on after a slight delay from M1 (as set by the internal 200nsec delay block). To ensure this delay, the gate resistor (RGATE) must be placed before the GATE pin of the IR25750L and the gate of M1. The GATE pin of the IR25750L and the gate of M1 are then connected together to form a single gate node.

When the gate drive signal of M1 goes low again, M1 turns off, and the gate of the HVFET gets discharged quickly through D1. The HVFET turns off again and blocks any high voltage occurring at the drain of M1. The CS output pin is then held at COM again through Q1. Assuming the drain of M1 is a typical high-voltage switching node that is connected to an inductor, the voltage signal produced at the CS output node will be the same sawtooth waveform that would result from using a traditional current sensing resistor placed at the source of M1 (**Figure 2**). The CS output pin can then be connected to a comparator circuit or used for any other desired current-sensing functions of a PWM controller or MCU circuit.





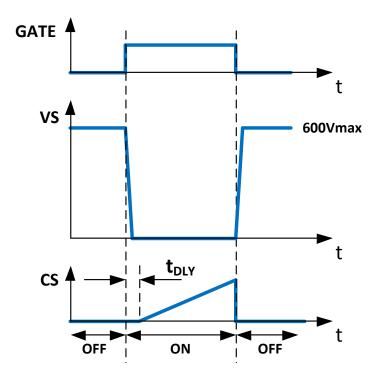


Figure 2: IR25750L timing diagram.

II. PCB Layout Guidelines

Since no VCC node is required for this circuit, the pcb layout becomes very simple to design (**Figure 3**). The IR25750L can be placed conveniently next to the power MOSFET or IGBT and connected easily to the existing pcb traces that are already used for the power switch (GATE, DRAIN, SOURCE). Only the CS trace needs to be routed back to the main PWM controller or MCU of the power supply circuit. Also, important to note, the power ground of the switching circuit must be separate from the COM connection of the IR25750L. The COM pin of the IR25750L should be connected to the source of the power MOSFET with a <u>single trace only</u>, and, the power ground <u>should not</u> be routed through the COM pin of the IR25750L.

A typical pcb layout is also shown for a DirectFET footprint (**Figure 4**). Again, the IR25750L can be placed directly next to the MOSFET and connected to the existing traces.



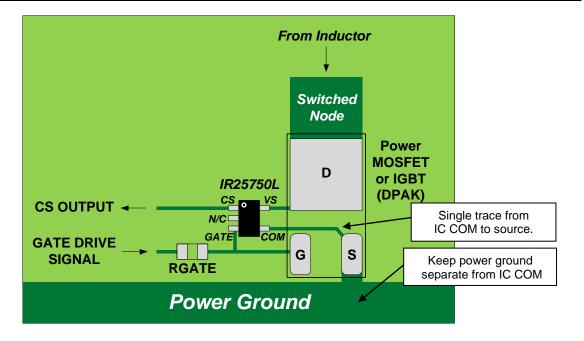


Figure 3: IR25750L typical pcb surface-mount layout (DPAK or D2PAK MOSFET or IGBT).

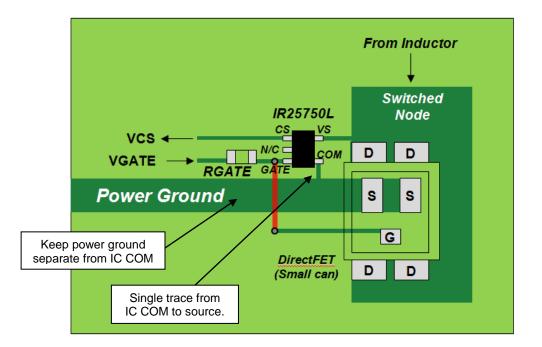


Figure 4: IR25750L typical pcb surface-mount layout (DirectFET).



III. Current Sensing Functionality

With the IR25750L connected properly in a switching circuit application, the waveforms (**Figure 4**) show the functionality of the circuit and the desired current sense signal at the CS pin. Compared to the conventional resistor sensing method, both methods match the actual current shape and both exhibit noise spikes due to switching. Proper filtering or digital blanking of the final PWM or MCU current sensing circuit will easily ignore these noise spikes to prevent any false triggering.

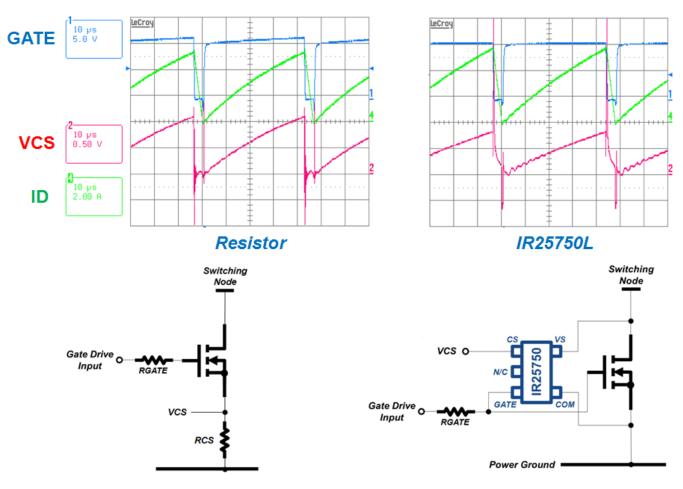
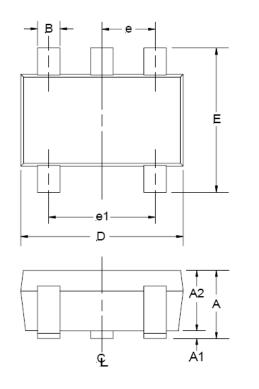
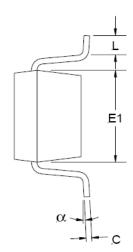


Figure 4: IR25750L switching waveforms vs. resistor method (green=IDRAIN, red=VCS, blue=GATE). (RCS=0.21 ohms, RDS(on)=0.18 ohms)



Package Details: 5L SOT-23



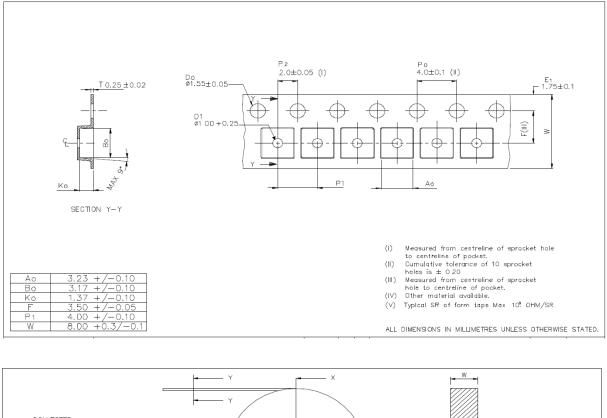


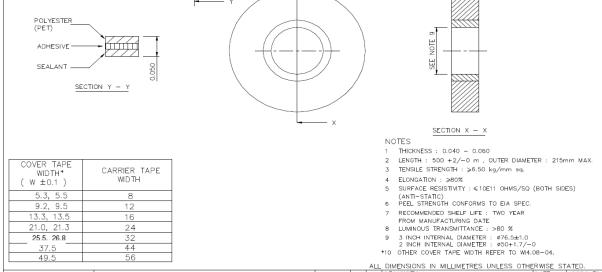
SYMBOL	MIN	MAX		
А	0.90	1.45		
A1	0.00	0.15		
A2	0.90	1.30		
В	0.25	0.50		
С	0.09	0.20		
D	2.80	3.00		
E	2.60	3.00		
E1	1.50	1.75		
е	0.95 REF			
e1	1.90 REF			
L	0.35	0.55		
α	08	108		

NOTE: ALL MEASUREMENTS ARE IN MILLIMETERS.



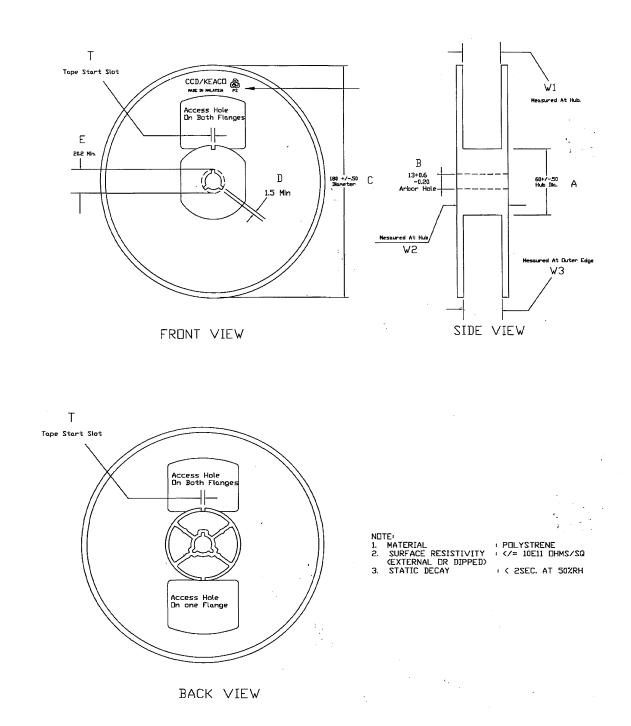
Tape and Reel Details: 5L SOT-23







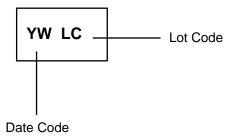
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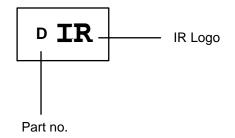


Part Marking Information: 5L SOT-23

Top Marking



Bottom Marking





Qualification Information[†]

Qualification Level		(pe	Industrial ^{††} (per JEDEC JESD 47)		
			Comments: This family of ICs has passed JEDEC's		
			Industrial qualification. IR's Consumer qualification level is		
		granted by extension	granted by extension of the higher Industrial level.		
Moisture Sensitivity Level		SOT-23	MSL1 ^{†††}		
		301-23	(per IPC/JEDEC J-STD-020)		
	Machine Model	Class A			
ESD		(per JEDEC standard EIA/JESD22-A115-A)			
230	Human Body Model	Class 1B			
		(per ANSI/ESDA/JEDEC standard JS-001-2012)			
IC Latch-Up Test			Class I, Level A		
			(per JESD78)		
RoHS Compliant			Yes		

+ Qualification standards can be found at International Rectifier's web site <u>http://www.irf.com/</u>

- ++ Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.
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